TOSHIBA Power Transistor Module Silicon NPN Epitaxial Type (Four Darlington Power Transistors 4 in One)

MP4013

High Power Switching Applications

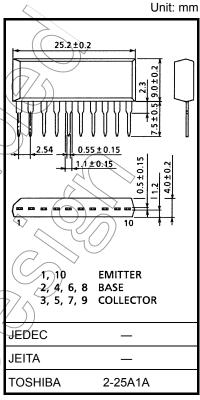
Hammer Drive, Pulse Motor Drive and Inductive Load Switching

- Small package by full molding (SIP 10 pins)
- High collector power dissipation (4-device operation) : $P_T = 4 \text{ W (Ta} = 25^{\circ}\text{C)}$
- High collector current: IC(DC) = 2 A (max)
- High DC current gain: $h_{FE} = 2000$ (min) ($V_{CE} = 2$ V, $I_{C} = 1$ A)
- Zener diode included between collector and base.

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V_{CBO}	80±10	V	
Collector-emitter voltage		V _{CEO}	80 ± 10	y	
Emitter-base voltage		V _{EBO}	8	//	
Collector current	DC	Ic	2	\ <u>\</u>	
	Pulse	ICP)) 3	A	
Continuous base current		lβ ∨	0.5	A	
Collector power dissipation		PC	2.0	NX.	
(1-device operation)			2.0	VV	
Collector power dissipati	on	PT	4.07	,	
(4-device operation)		~ ` `)	(*// 5)	VV	
Junction temperature		Tj	150	°C	
Storage temperature ran	ge	T _{stg}	-55 to 150	°C	

Industrial Applications

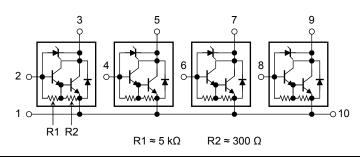


Weight: 2.1 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design/the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Denating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Array Configuration



MP4013

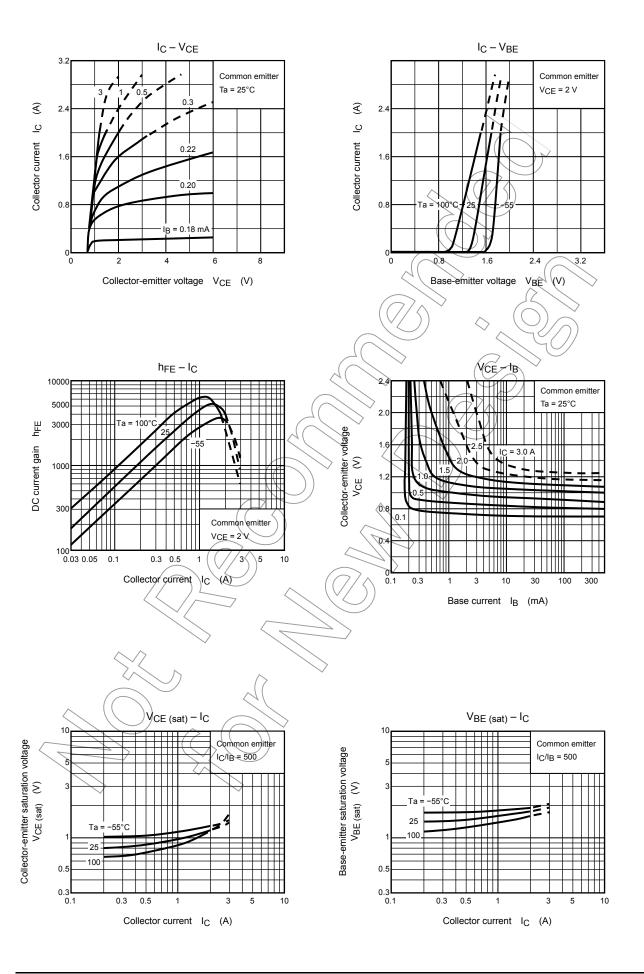
Thermal Characteristics

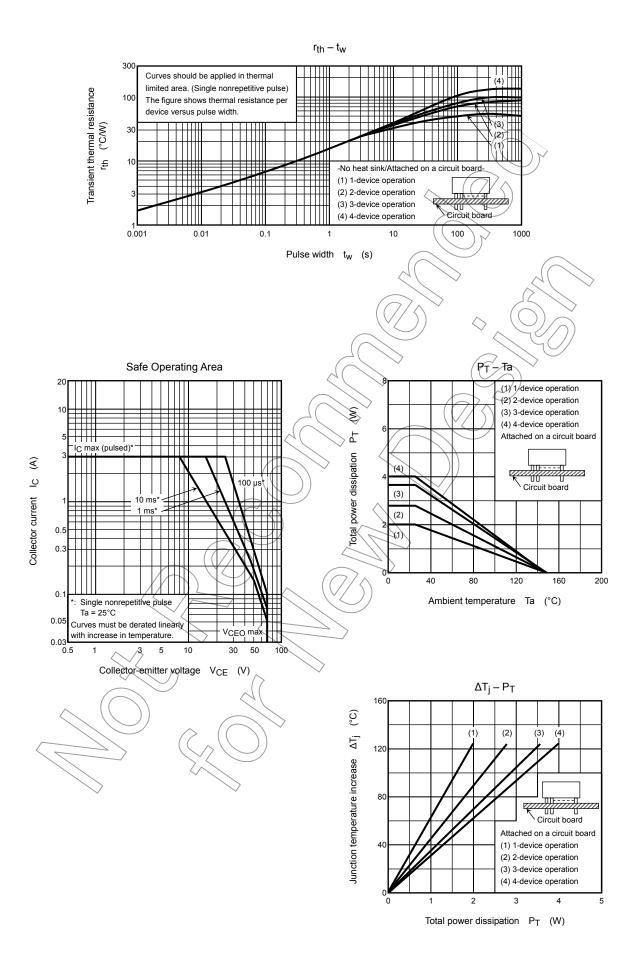
Characteristics	Symbol	Max	Unit	
Thermal resistance from junction to ambient	ΣR _{th (j-a)}	31.3	°C/W	
(4 devices operation, Ta = 25°C)	,			
Maximum lead temperature for soldering purposes	TL	260	°C	
(3.2 mm from case for 10 s)				

Electrical Characteristics (Ta = 25°C)

Charac	teristics	Symbol	Test Condition	Min	Тур.	Max	Unit	
Collector cut-off cu	rrent	I _{CBO}	V _{CB} = 60 V, I _E = 0 A	_		10	μΑ	
Collector cut-off cu	rrent	I _{CEO}	V _{CE} = 60 V, I _B = 0 A	- /	4	10	μΑ	
Emitter cut-off current		I _{EBO}	V _{EB} = 8 V, I _C = 0 A	0.8	/-/	> 4.0	mA	
Collector-base breakdown voltage		V (BR) CBO	I _C = 100 μA, I _E = 0 A	70	80	90	٧	
Collector-emitter br	reakdown voltage	V (BR) CEO	I _C = 10 mA, I _B = 0 A	70	80/	90	V	
DC current gain		h _{FE (1)}	V _{CE} = 2(V, 1 _C = 1 A	2000	√ –	_	_	
Saturation voltage	Collector-emitter	V _{CE} (sat)	I _C = 1 A, I _B = 1 mA		_	1.5	V	
	Base-emitter	V _{BE} (sat)	Ic = 1 A, B = 1 mA	\ _	_	2.0		
Transition frequency		f _T	V _{CE} = 2V, I _C = 0.5 A	/ _	100	_	MHz	
Collector output capacitance		C _{ob}	V _{CB} = 10 V, I _E = 0 A, f = 1MHz	_	20	_	pF	
Switching time	Turn-on time	ton	Input IB1 Output		0.4			
	Storage time	tstg	20 μs B2 VCC = 30 V	ı	4.0	ı	μs	
	Fall time) t _f	I _{B1} = -I _{B2} = 1 mA, duty cycle ≤ 1%	1	0.6			

MP4013 Part No. (or abbreviation code) Lot No. A line indicates lead (Pb)-free package or lead (Pb)-free finish.





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